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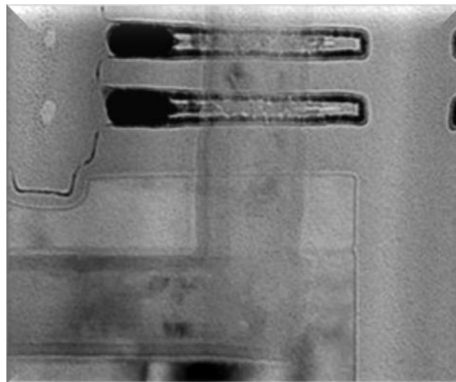
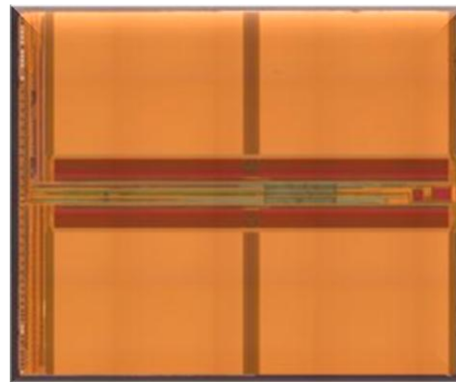
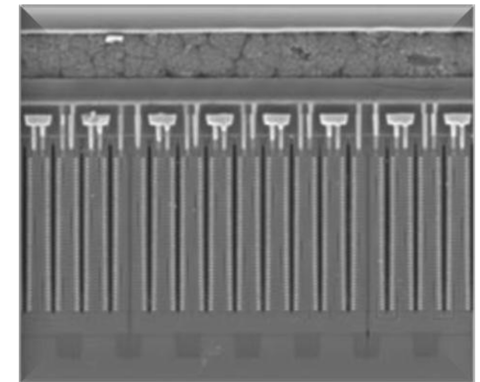
H26M51002HPR

SK Hynix 3D NAND FLASH (Ver.2)







Product Analysis Report

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To Know

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